



HUFA75829D3S Information



For Reference Only

Part Number HUFA75829D3S

Manufacturer Fairchild/ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

DescriptionMOSFET N-CH 150V 18A DPAK**Package**TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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HUFA75829D3S Specifications

Manufacturer Part Number HUFA75829D38 Manufacturer Fairchild/ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series UltraFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 150V Current - Continuous Drain (Id) @ 25°C 18A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 70nC @ 20V Input Capacitance (Ciss) (Max) @ Vds 1080pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 110W (Tc) Rds On (Max) @ Id, Vgs 110 mOhm @ 18A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252AA Package / Case TO-252A, DPak (2 Leads + Tab), SC-63		
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SeriesUltraFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C18A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs70nC @ 20VInput Capacitance (Ciss) (Max) @ Vds1080pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs110 mOhm @ 18A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252AAPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C18A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs70nC @ 20VInput Capacitance (Ciss) (Max) @ Vds1080pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs110 mOhm @ 18A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252AAPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C18A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs70nC @ 20VInput Capacitance (Ciss) (Max) @ Vds1080pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs110 mOhm @ 18A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252AAPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	UltraFET?
Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C18A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs70nC @ 20VInput Capacitance (Ciss) (Max) @ Vds1080pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs110 mOhm @ 18A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252AAPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 18A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 18A (Tc) 110V TOC 2504A 10V 255°C ~ 175°C (TJ)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs70nC @ 20VInput Capacitance (Ciss) (Max) @ Vds1080pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs110 mOhm @ 18A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252AAPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	150V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature - Power Dissipation (Max) Inouch (Max) @ Id, Vgs Inouch (Max) Inouch (Max)	Current - Continuous Drain (Id) @ 25°C	18A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 18A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252-AA Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 18A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252-AA Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ± 20 VFET Feature-Power Dissipation (Max) 110 W (Tc)Rds On (Max) @ Id, Vgs 110 mOhm @ 18 A, 10 VOperating Temperature -55° C $\sim 175^{\circ}$ C (TJ)Mounting TypeSurface MountSupplier Device PackageTO- 252 AAPackage / CaseTO- 252 -3, DPak (2 Leads + Tab), SC- 63	Gate Charge (Qg) (Max) @ Vgs	70nC @ 20V
FET Feature - Power Dissipation (Max) 110W (Tc) Rds On (Max) @ Id, Vgs 110 mOhm @ 18A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252AA Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	1080pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 18A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252AA Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs110 mOhm @ 18A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252AAPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount TO-252AA Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	110W (Tc)
Mounting Type Surface Mount TO-252AA Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	110 mOhm @ 18A, 10V
Supplier Device Package TO-252AA Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	TO-252AA
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

HUFA75829D3S Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

HUFA75829D3S Payment Methods



















HUFA75829D3S Shipping Methods













If you have any question about HUFA75829D3S, please do not hesitate to contact us!

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